

1944-1945

#3

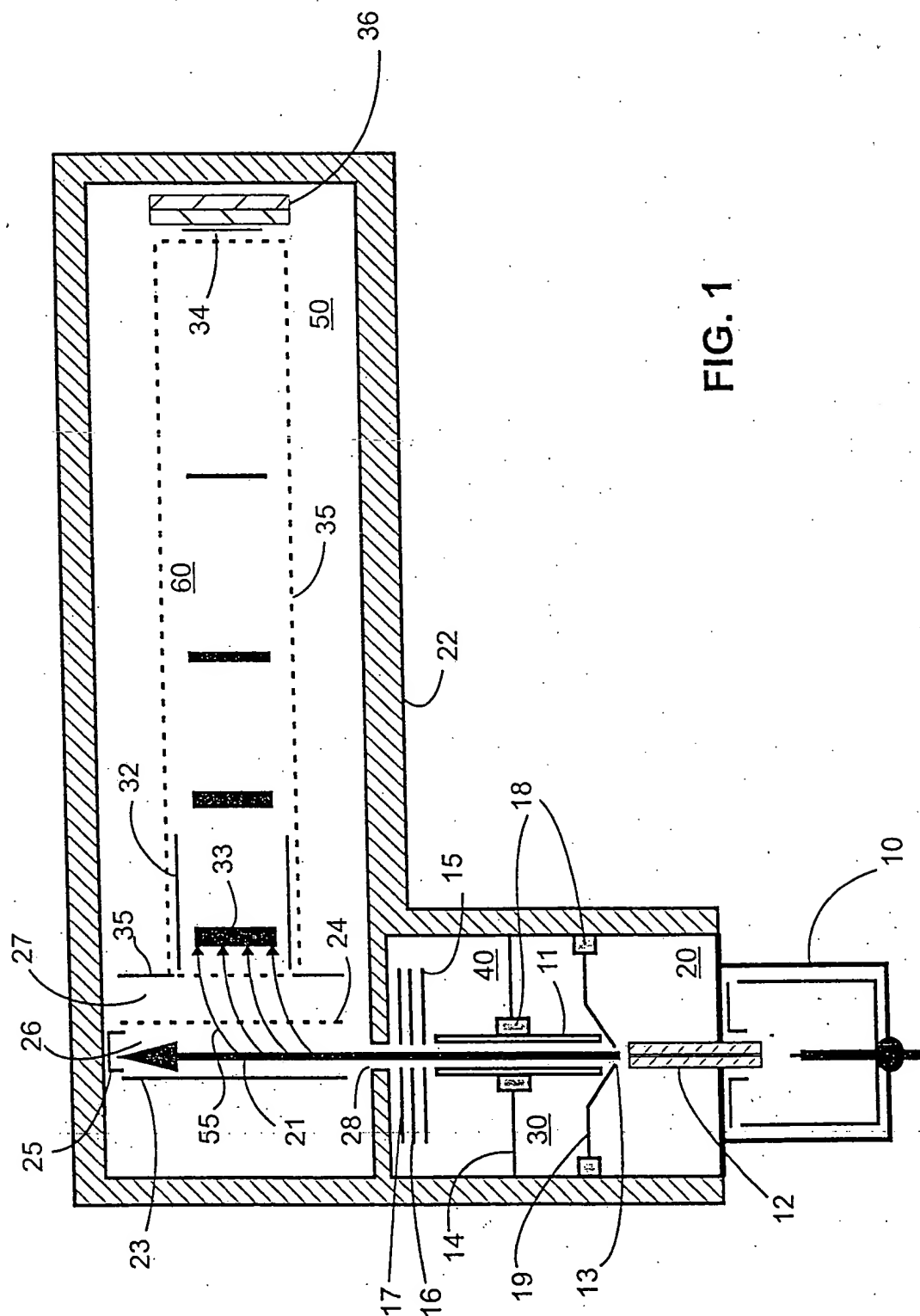


FIG. 1

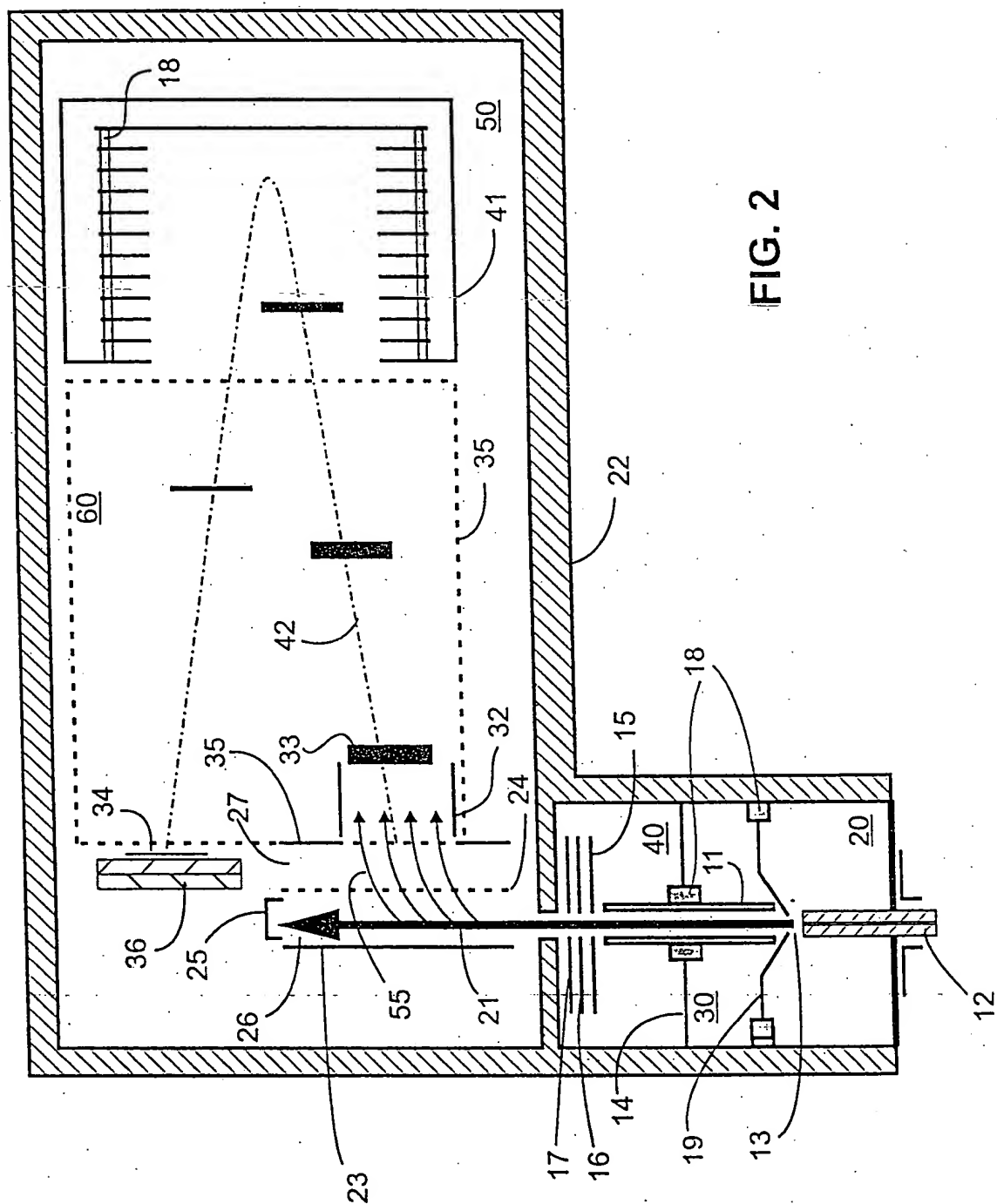


FIG. 2

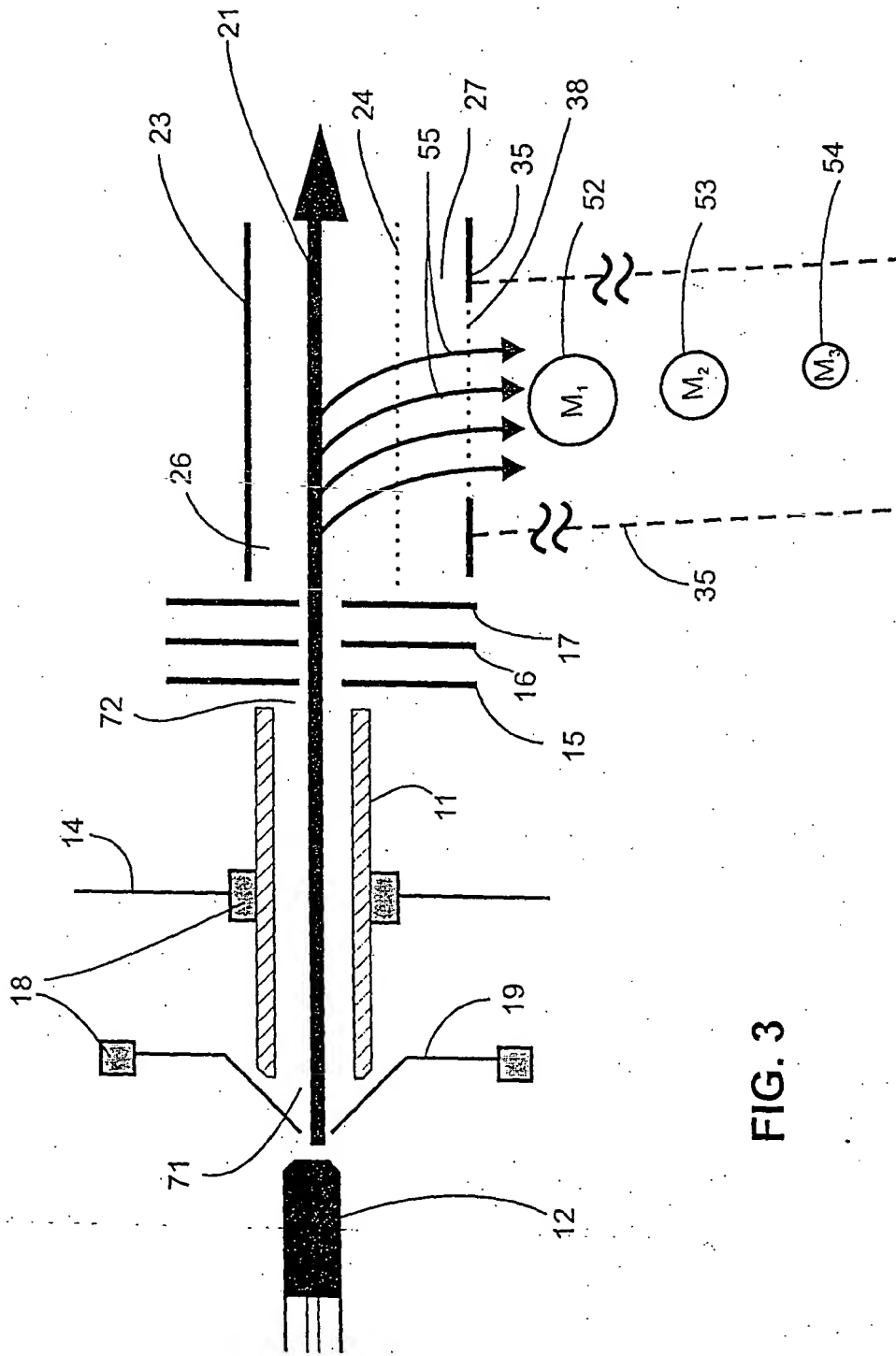


FIG. 3

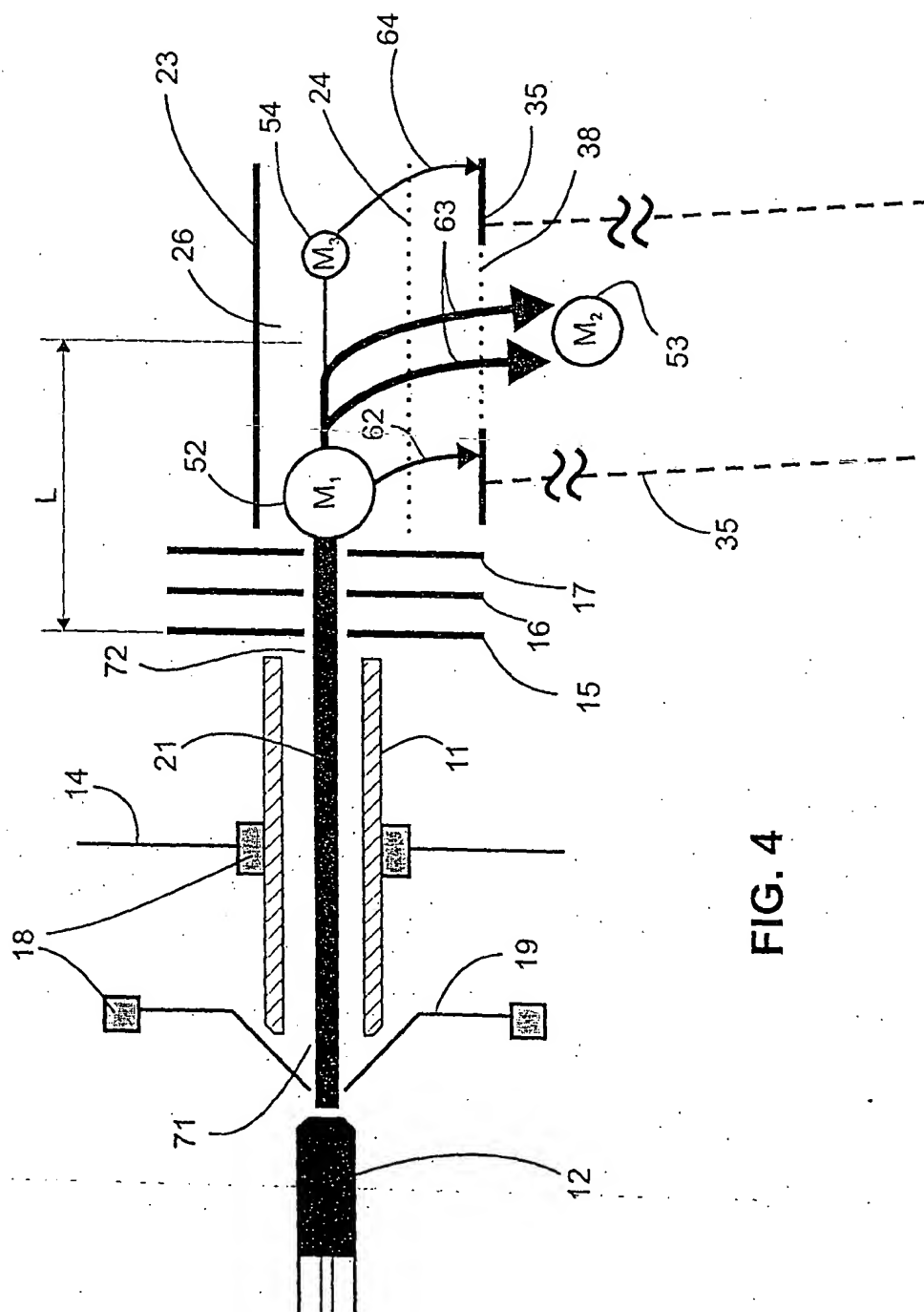


FIG. 4

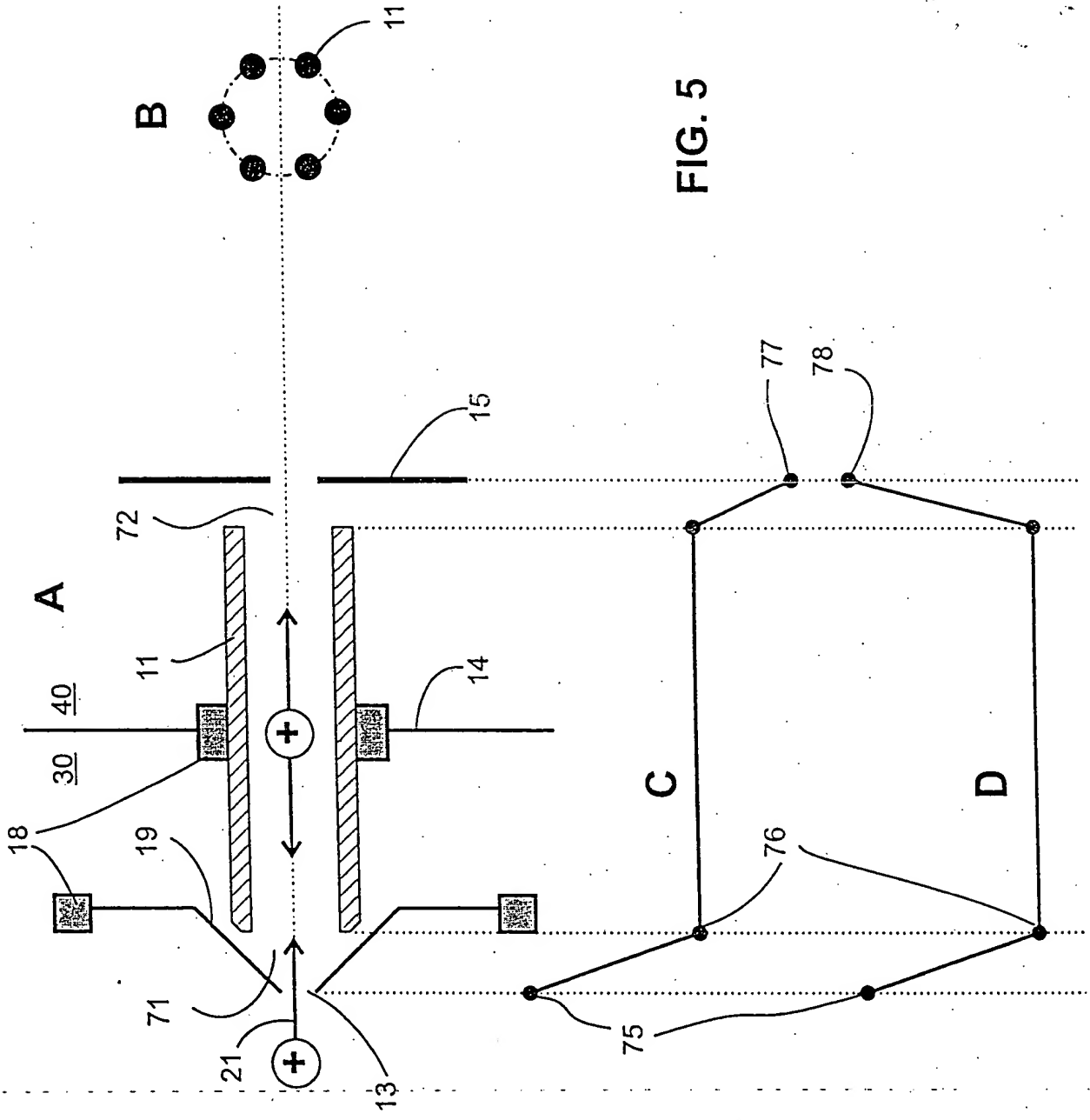


FIG. 5

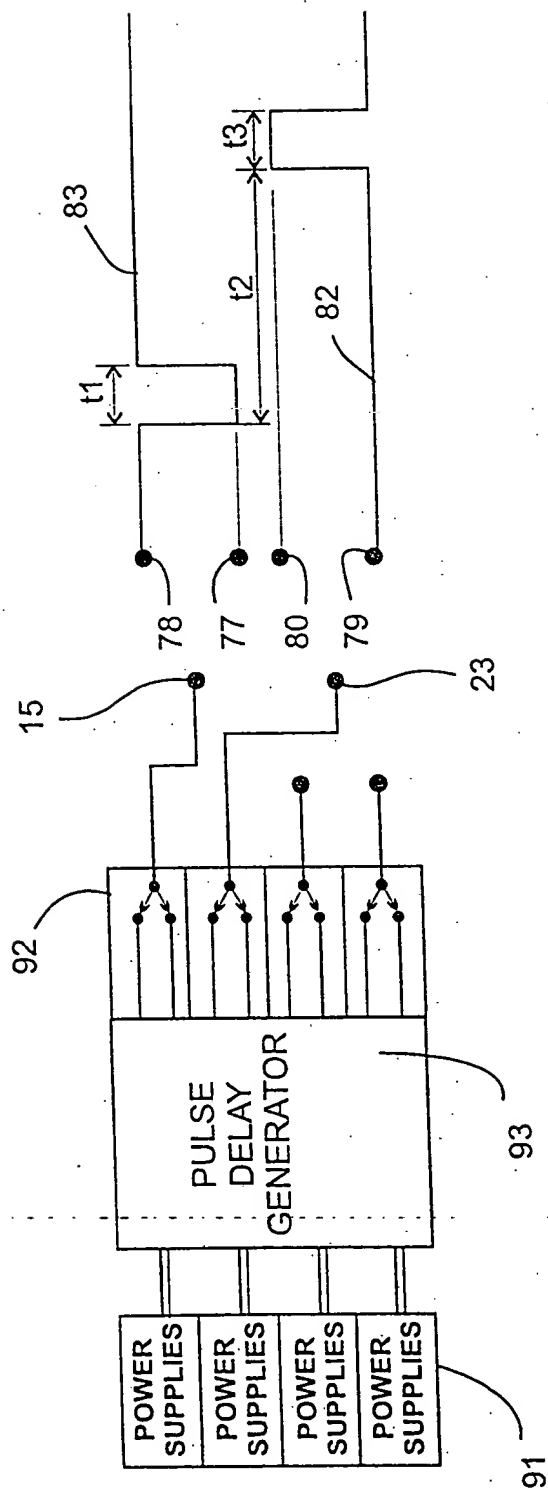


FIG. 6

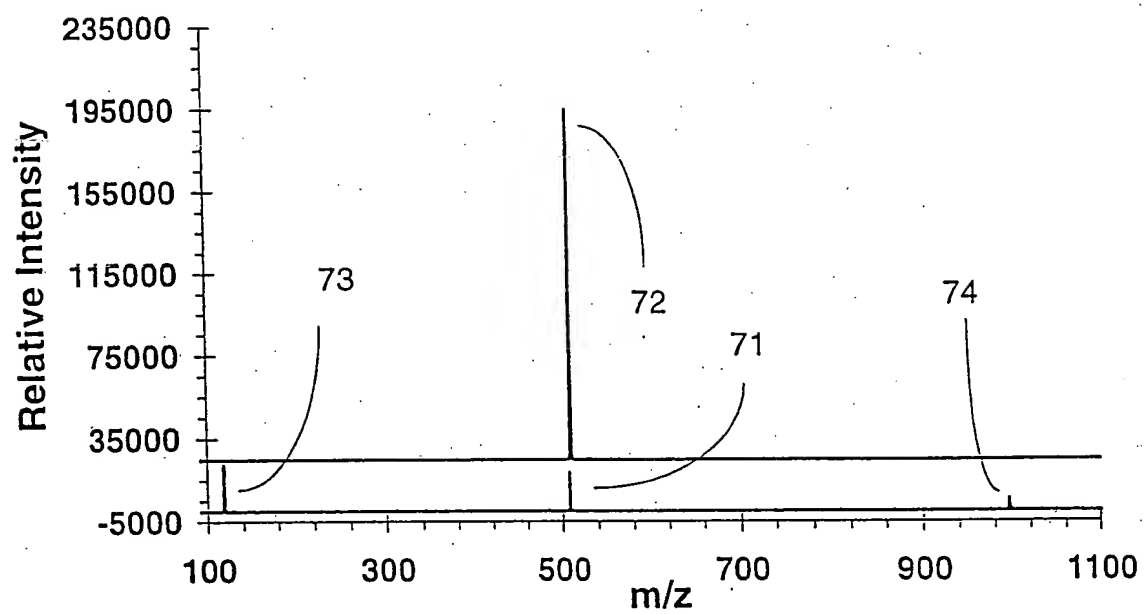


FIG. 7A

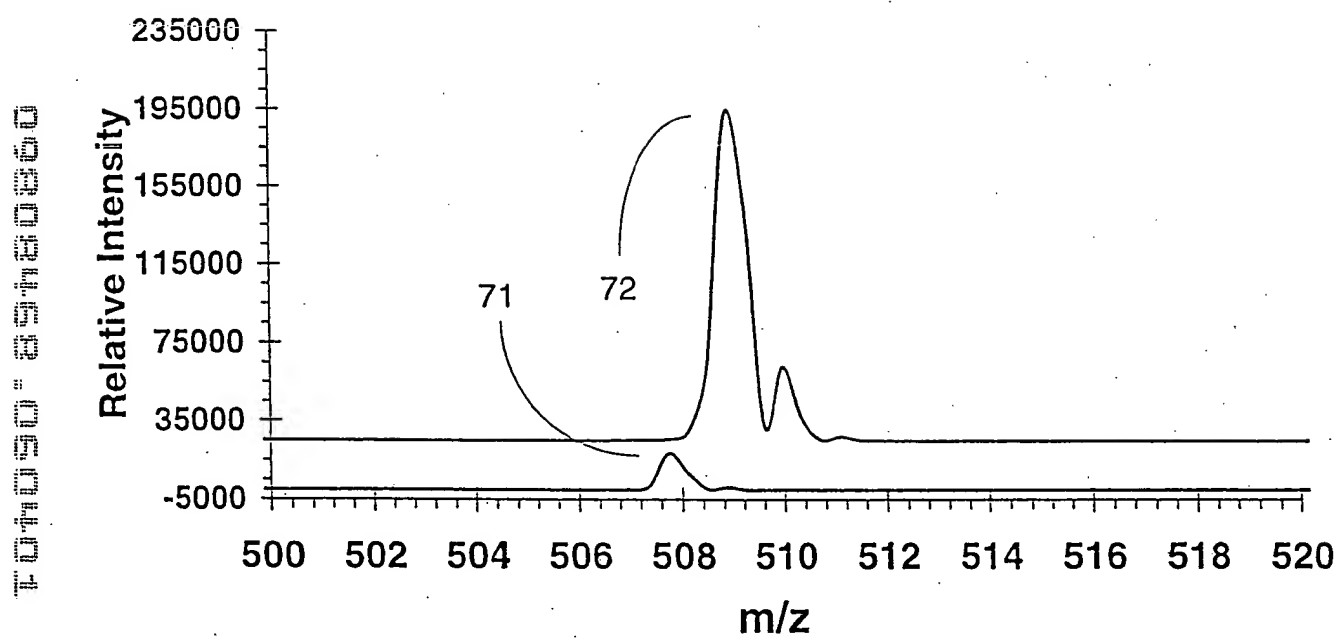


FIG. 7B

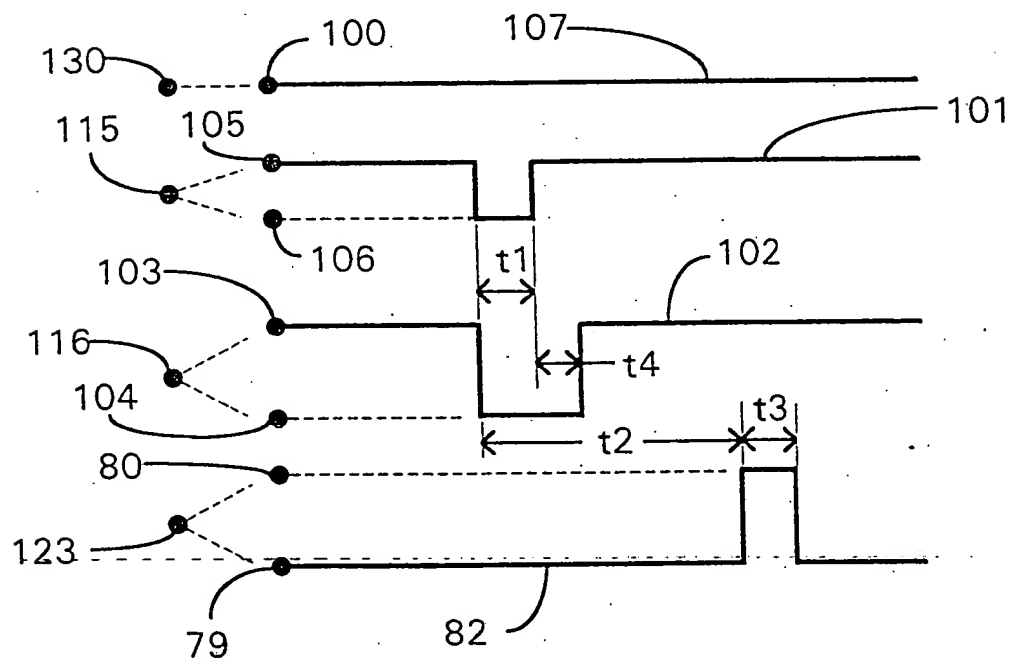
[illegible]

B

FIG. 9

This diagram shows a cross-sectional view of a semiconductor device. It features a central trench structure. The top layer is labeled 107. Below it is a layer 101. A layer 102 is located on the right side of the trench. The trench itself is defined by a central region 100 and side regions 105 and 106. The bottom of the trench is labeled 80. The bottom layer is labeled 82. Various other labels include 130, 115, 103, 116, 104, 123, 79, and 107. Dimensions t1, t2, and t3 are indicated with arrows. Dashed lines connect the labels to their corresponding features.

A



B

FIG. 10

B

A schematic diagram of a multi-channel device. On the left, a black rectangular block with three horizontal lines extending from its left side has an arrow pointing to the right. This arrow points towards three parallel horizontal channels. The top and bottom channels are outlined with solid lines, while the middle channel is filled with a cross-hatch pattern. These channels are separated by vertical lines. To the right of these channels is a cross-sectional view of a device. It shows a top layer (150) with a hatched pattern, a middle layer (151) with a vertical line pattern, and a bottom layer (152) with a horizontal line pattern. Below these layers are four curved lines (153, 154) representing a substrate or base. Arrows point from the top layer (150) down to the curved lines (153, 154). A label 35 is positioned to the right of the curved lines.

C

FIG. 11

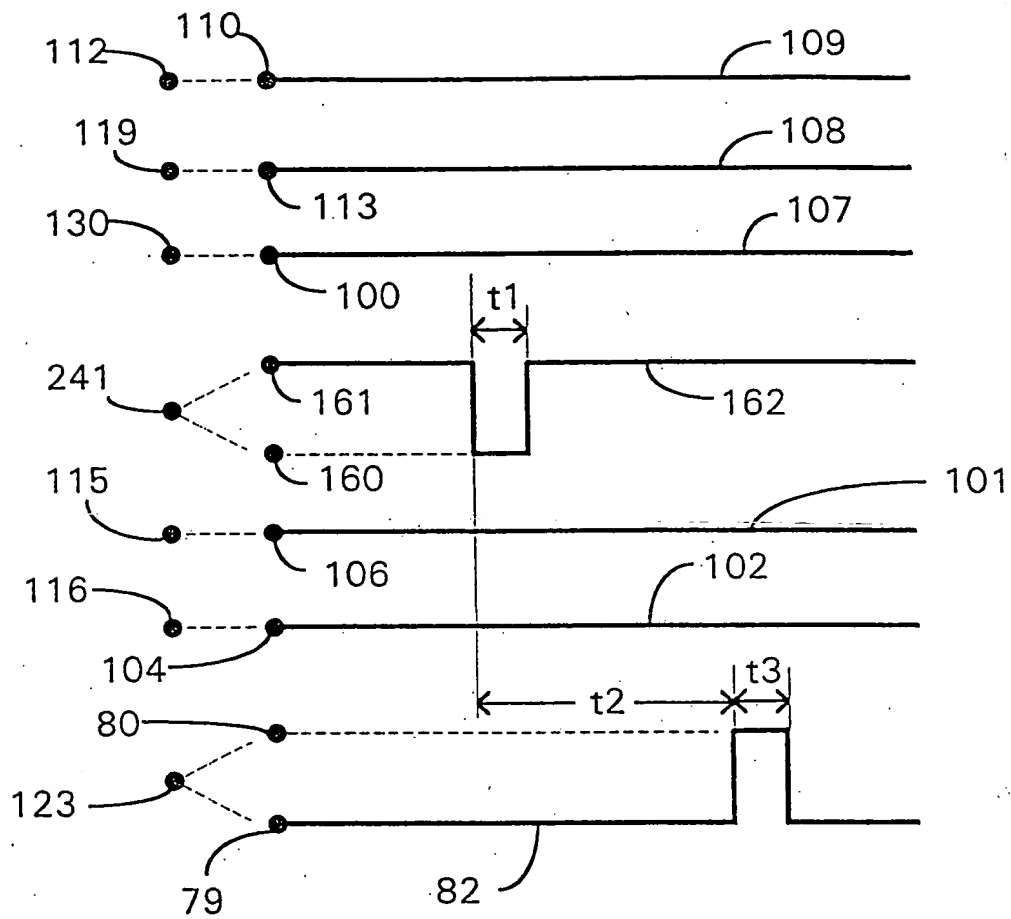


FIG. 12